

FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 05-720-US2	Serial No. 10/559,981
<p align="center">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p align="center">(Use several sheets if necessary)</p>		Applicant: Kouvetakis, et al.	
		Filing Date: December 8, 2005	Group: 2812

RSP	70.	R. Gaska, A. Zukauskas, M. S. Shur, and M. A. Khan, "Progress in III-nitride based white light sources", Proceedings of the SPIE, Vol: 4776, pp. 82-96 (2002).
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EXAMINER <i>R. S. Darty</i>	DATE CONSIDERED 4/19/07
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.